1763 #2

**PATENT**

Case Docket No. ASMJP.090AUS
Date: January 11, 2002

IDS
12-1-03
returned

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

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| Applicant(s) | : | Todd, et al. |
| Appl. No. | : | 09/993,024 |
| Filed | : | November 13, 2001 |
| For | : | LOW-K DIELECTRIC MATERIALS AND PROCESSES |
| Examiner | : | Unknown |
| Group Art Unit | : | 1763 |

I hereby certify that this correspondence and all marked attachments are being deposited with the United States Postal Service as first class mail in an envelope addressed to: Assistant Commissioner for Patents, Washington, D.C. 20231, on

January 11, 2002
(Date)

Joseph J. Mallon, Reg. No. 39,287



**TRANSMITTAL LETTER**

**ASSISTANT COMMISSIONER FOR PATENTS**
**WASHINGTON, D.C. 20231**
ATTENTION: APPLICATION BRANCH

Dear Sir:

Enclosed for filing in the above-identified application are:

(X) An Information Disclosure Statement.

(X) A PTO Form 1449 with Sixty-seven (67) references.

(X) The Commissioner is hereby authorized to charge any additional fees which may be required, or credit any overpayment, to Account No. 11-1410.

(X) Return prepaid postcard.

Joseph J. Mallon
Registration No. 39,287
Attorney of Record

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ASMJP.090AUS

PATENT

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**



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| Applicant | : | Todd, et al. | ) | Group Art Unit 1763 |
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| For | : | LOW-K DIELECTRIC MATERIALS AND PROCESSES | ) | |
| Examiner | : | Unknown | ) | |

INFORMATION DISCLOSURE STATEMENT

Assistant Commissioner for Patents
Washington, D.C. 20231

Dear Sir:

Enclosed is form PTO-1449 listing references that are also enclosed. This Information Disclosure Statement is being filed before the receipt of a first Office Action on the merits, and presumably no fee is required in accordance with 37 C.F.R. § 1.97(b)(3). If a first Office Action on the merits was mailed before the mailing date of this Statement, the Commissioner is authorized to charge the fee set forth in 37 C.F.R. § 1.17(p) to Deposit Account No. 11-1410.

Respectfully submitted,

KNOBBE, MARTENS, OLSON & BEAR, LLP

Dated: 1/11/02

By: Joseph J. Mallon

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| FORM PTO-1449 U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE | ATTY. DOCKET NO. ASMJP.090AUS | APPLICATION NO. 09/993,024 |
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| **INFORMATION DISCLOSURE STATEMENT BY APPLICANT** (USE SEVERAL SHEETS IF NECESSARY) | APPLICANT Todd, et al. | |
| | FILING DATE November 13, 2001 | GROUP 1763 |



**U.S. PATENT DOCUMENTS**

| EXAMINER INITIAL | | DOCUMENT NUMBER | DATE | NAME | CLASS | SUBCLASS | FILING DATE (IF APPROPRIATE) |
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| EXAMINER | DATE CONSIDERED |
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***EXAMINER:** INITIAL IF CITATION CONSIDERED, WHETHER OR NOT CITATION IS IN CONFORMANCE WITH MPEP 609; DRAW LINE THROUGH CITATION IF NOT IN CONFORMANCE AND NOT CONSIDERED, INCLUDE COPY OF THIS FORM WITH NEXT COMMUNICATION TO APPLICANT.

| FORM PTO-1449 U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE | ATTY. DOCKET NO. ASMJP.090AUS | APPLICATION NO. 09/993,024 |
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**FOREIGN PATENT DOCUMENTS**

| EXAMINER INITIAL | | DOCUMENT NUMBER | DATE | COUNTRY | CLASS | SUBCLASS | TRANSLATION YES | TRANSLATION NO |
|---|---|---|---|---|---|---|---|---|
| | 27. | WO 97/41592 | 11/06/1997 | PCT | | | | |
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| EXAMINER INITIAL | | OTHER DOCUMENTS (INCLUDING AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC.) |
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